

### SURFACE MOUNT SILICON DUAL, MATCHED NPN TRANSISTOR



• Device is Halogen Free by design

# cen' Semiconductor Corp.

www.centralsemi.com

# **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLT5088EM consists of two individual, isolated 5088E NPN silicon transistors with matched  $V_{BE(ON)}$  characteristics. This device is designed for applications requiring high gain and low noise.

### **MARKING CODE: 88M**

## FEATURES:

Transistor pair matched for VBE(ON)

MAXIMUM RATINGS: (T <sub>A</sub> =25°C)	SYMBOL		UNITS
Collector-Base Voltage	VCBO	50	V
Collector-Emitter Voltage	VCEO	50	V
Emitter-Base Voltage	VEBO	5.0	V
Continuous Collector Current	IC	100	mA
Power Dissipation	PD	350	mW
Operating and Storage Junction Temperature	т <sub>Ј</sub> , т <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	$\Theta_{JA}$	357	°C/W

### ELECTRICAL CHARACTERISTICS PER TRANSISTOR: (T<sub>A</sub>=25°C unless otherwise noted)

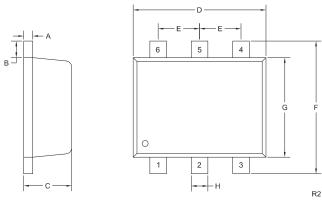
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS		
ICBO	V <sub>CB</sub> =20V			50	nA		
IEBO	V <sub>EB</sub> =3.0V			50	nA		
BVCBO	I <sub>C</sub> =100μA	50	135		V		
BVCEO	I <sub>C</sub> =1.0mA	50	65		V		
BVEBO	Ι <sub>Ε</sub> =100μΑ	5.0	8.7		V		
V <sub>CE</sub> (SAT)	I <sub>C</sub> =10mA, I <sub>B</sub> =1.0mA		45	100	mV		
VCE(SAT)	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA		110	400	mV		
VBE(SAT)	I <sub>C</sub> =10mA, I <sub>B</sub> =1.0mA		700	800	mV		
h <sub>FE</sub> `´	V <sub>CE</sub> =5.0V, I <sub>C</sub> =0.1mA	300	430	900			
hFE	V <sub>CE</sub> =5.0V, I <sub>C</sub> =1.0mA	300	435				
hFE	V <sub>CE</sub> =5.0V, I <sub>C</sub> =10mA	300	430				
hFE	V <sub>CE</sub> =5.0V, I <sub>C</sub> =100mA	50	125				
fT	V <sub>CE</sub> =5.0V, I <sub>C</sub> =500µA, f=20MHz	100			MHz		
Cob	V <sub>CB</sub> =5.0V, I <sub>E</sub> =0, f=1.0MHz			4.0	pF		
C <sub>ib</sub>	V <sub>BE</sub> =0.5V, I <sub>C</sub> =0, f=1.0MHz			15	pF		
h <sub>fe</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =1.0mA, f=1.0kHz	350		1400			
NF	V <sub>CE</sub> =5.0V, I <sub>C</sub> =100μA, R <sub>S</sub> =10kΩ						
	f=10Hz to 15.7kHz			3.0	dB		
MATCHING CHARACTERISTICS:							
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS			
VBE1-VBE2	V <sub>CE</sub> =5.0V, I <sub>C</sub> =1.0μA		10	mV			
VBE1-VBE2	V <sub>CE</sub> =5.0V, I <sub>C</sub> =5.0µA		10	mV			
VBE1-VBE2	V <sub>CE</sub> =5.0V, I <sub>C</sub> =10µA		10	mV			
VBE1-VBE2	V <sub>CE</sub> =5.0V, I <sub>C</sub> =100µA		10	mV			

R3 (29-June 2015)





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CMLT5088EM Typical VBE(ON)

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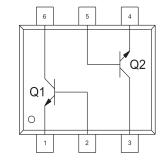
1

0.1

I<sub>C</sub>, Collector Current (mA)

#### DIMENSIONS INCHES MILLIMETERS MIN MAX 0.07 0.18 SYMBOL MIN MAX 0.0027 0.007 0.07 Α 0.008 B C 0.20 0.017 0.024 0.45 0.60 D 0.059 0.067 1.50 1.70 Е 0.020 0.50 F 0.059 0.067 1.50 1.70 0.000 0.001 1.00 1.10 1.30 0.043 0.051 1.10 1.30 0.006 0.012 0.15 0.30 G Н SOT-563 (REV: R2)

### PIN CONFIGURATION



### LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q24) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

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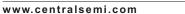
111

10

V<sub>CE</sub>=5.0V

T<sub>A</sub>=25°C

100



850

800

750

700

650

600

550

500

450

400

V, Voltage (mV)

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0.01

# SOT-563 CASE - MECHANICAL OUTLINE

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### CMLT5088EM



### SURFACE MOUNT SILICON DUAL, MATCHED NPN TRANSISTOR

### SERVICES

- · Bonded Inventory
- Custom Electrical Screening
- Custom Electrical Characteristic Curves
- SPICE Models
- Custom Packaging
- Package Base Options
- Custom Device Development/Multi Discrete Modules (MDM™)
- Bare Die Available for Hybrid Applications

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